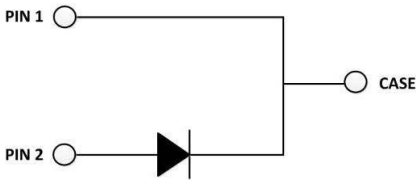
3rd Generation 1200V/15A SiC Schottky Barrier Diode

Features

- Revolutionary semiconductor material - Silicon Carbide (SiC)
- No reverse recovery
- High-speed switching performance
- Temperature-independent switching behavior
- System cost / size savings due to reduced cooling requirements
- Junction temperature range from -55℃ to 175℃
- RoHS compliant



Package Type: TO-247-2L

Potential Applications

- Industrial power supplies: Industrial UPS
- Battery chargers
- Solar inverters
- Switch mode power supplies

Description

The SDS120J015H3 SiC Schottky Barrier Diode (SBD) has been developed using Sanan's advanced 3rd generation SiC SBD technology with the highest performance and reliability. It registers higher efficiency, higher operation temperature and lower loss and can be operated at higher frequency than Si-based solutions. As to the Schottky structure, it shows no recovery at turn-off and allows a low leakage current with reverse voltage up to 1200V. It can contribute to system miniaturization and achieve lightweight system design. Using RoHS compliant components, it is qualified for use in industrial application.

Product Specifications

Device	V_{RRM}	I_F (135℃)	V_F (25℃)	Q_C	Marking
SDS120J015H3	1200V	23A	1.35V	82nC	DS120015H3

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Table 1. Maximum Ratings

(Tc = 25℃, unless otherwise specified)

Parameter	Symbol	Value	Unit	Test conditions
Repetitive peak reverse voltage	V_{RRM}	1200	V	T_C = 25℃
Surge peak reverse voltage	V_{RSM}	1200		T_C = 25℃
DC reverse voltage	V_{DC}	1200		T_C = 25℃
Continuous forward current	I_F	51	A	T_C = 25℃
		23		T_C = 135℃
		15		T_C = 155℃
Surge non-repetitive forward current	I_{FSM}	140	A	T_C = 25℃, t_p = 10ms, half sine pulse
Surge repetitive forward current	I_{FRM}	90	A	T_C = 25℃, t_p = 10ms, half sine wave D = 0.1
Power dissipation	P_{tot}	234	W	T_C = 25℃
i^2t value	$\int i^2dt$	98	A^2s	T_C = 25℃, t_p = 10ms
Operating junction temperature	T_j	-55~175	℃	
Storage temperature	T_{stg}	-55~175	℃	
Mounting torque	M	1	Nm	M3 screw

Table 2. Thermal Resistance

Parameter	Symbol	Values			Unit	Test condition
		Min.	Typ.	Max.		
Thermal resistance from junction to case	$R_{th(j-c)}$	/	0.64	/	℃/W	

Table 3. Static Electrical Characteristics

(T_j = 25℃, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
DC blocking voltage	V_{DC}	1200	/	/	V	I_R = 100 μA
Forward voltage	V_F	/	1.35	1.50	V	I_F = 15A, T_j = 25℃
		/	1.85	2.20		I_F = 15A, T_j = 175℃
Reverse current	I_R	/	2	45	μA	V_R = 1200V, T_j = 25℃
		/	15	240		V_R = 1200V, T_j = 175℃

Table 4. Dynamic Electrical Characteristics

(T_j = 25℃, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
Total capacitance	C	/	1182	/	pF	V_R = 0V, f = 1MHz
		/	78	/		V_R = 400V, f = 1MHz
		/	57	/		V_R = 800V, f = 1MHz
Total capacitive charge	Q_C	/	82	/	nC	V_R = 800V
Capacitance stored energy	E_C	/	24	/	μJ	V_R = 800V

Electrical Characteristic Diagrams

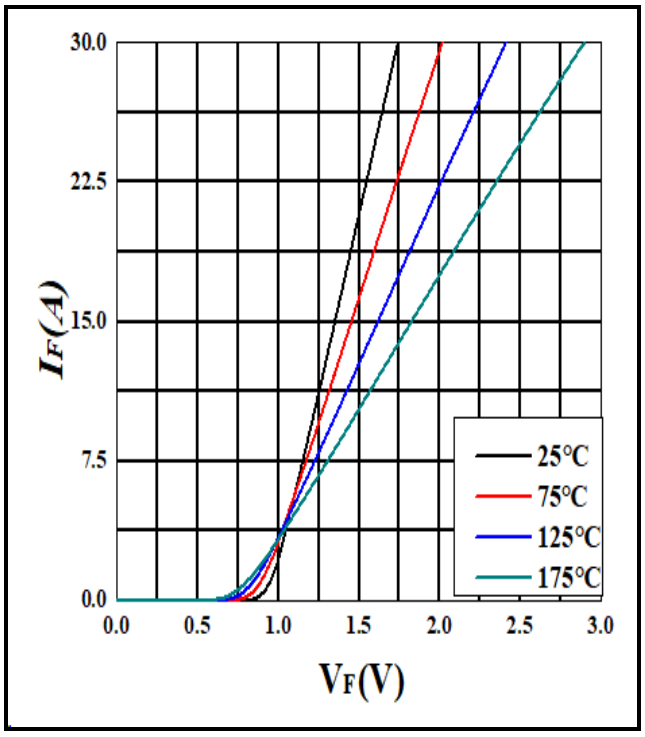


Figure 1. Forward characteristics

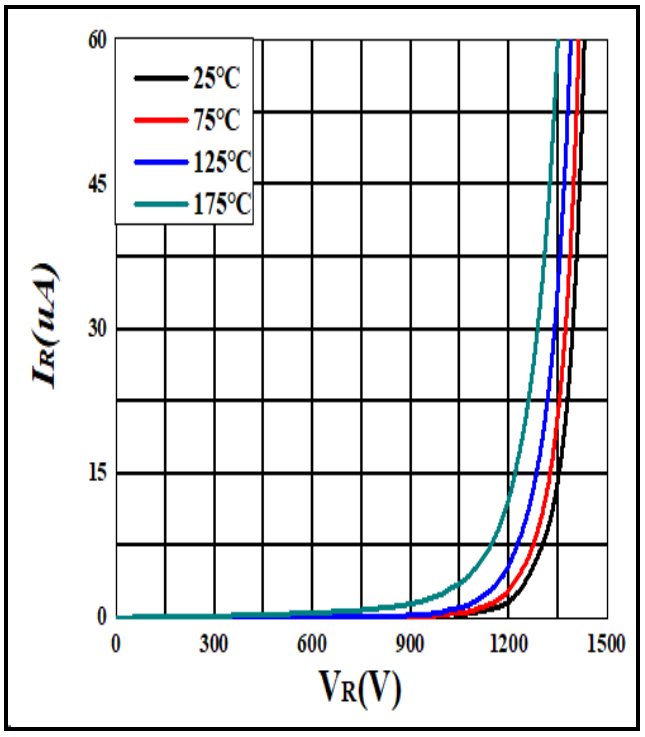


Figure 2. Reverse characteristics

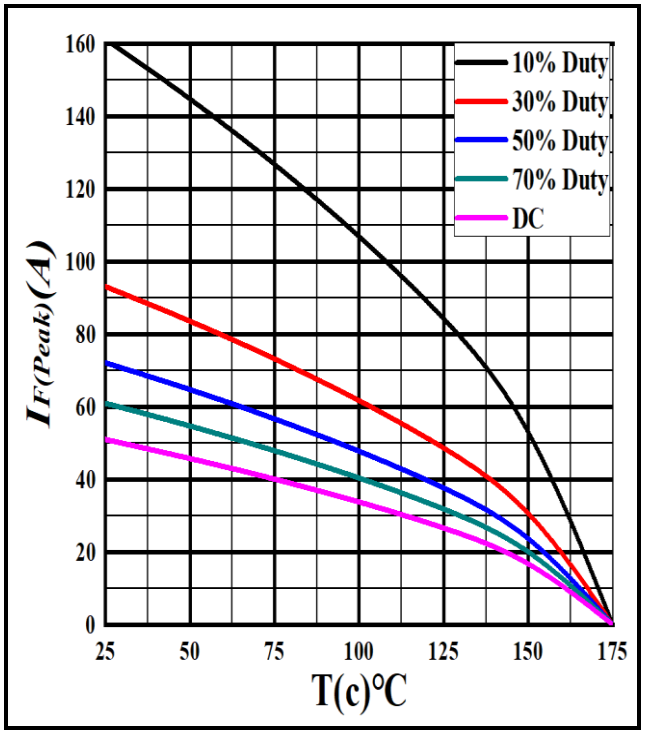


Figure 3. Current derating

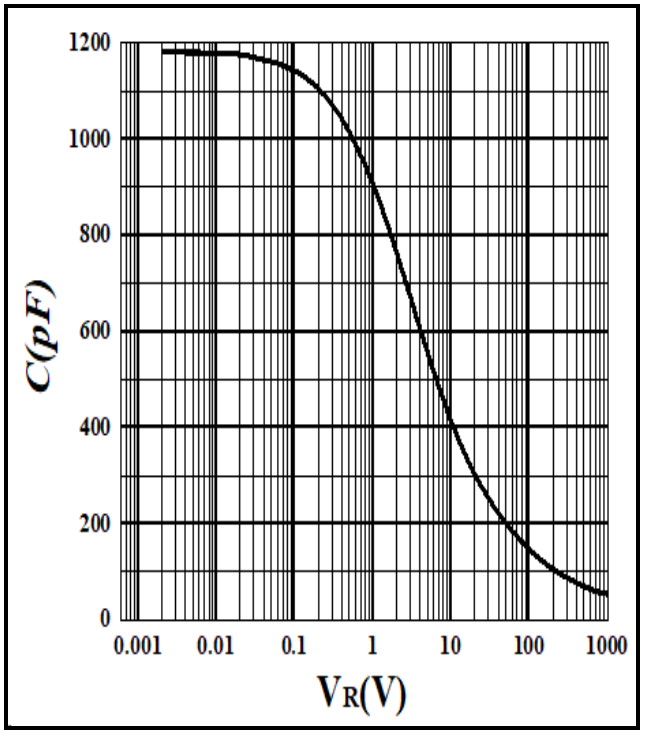


Figure 4. Capacitance vs. reverse voltage

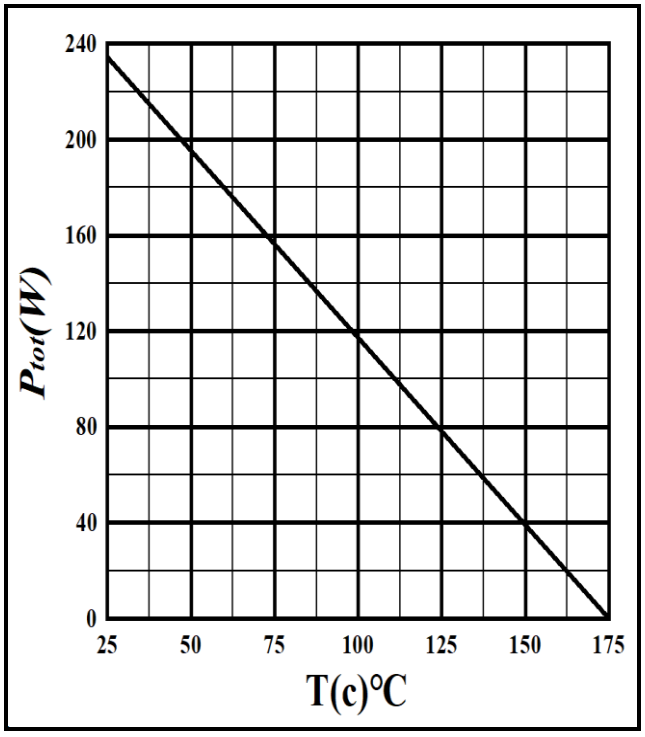


Figure 5. Power derating

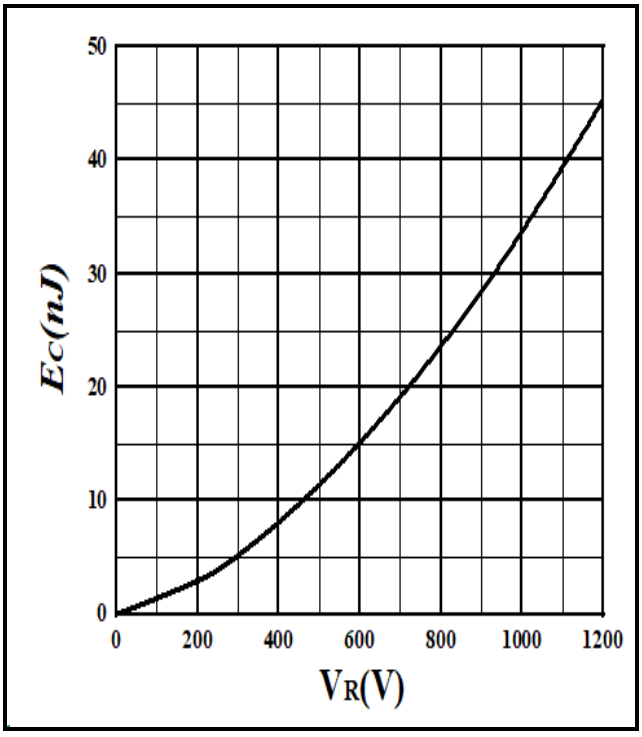


Figure 6. Capacitance stored energy

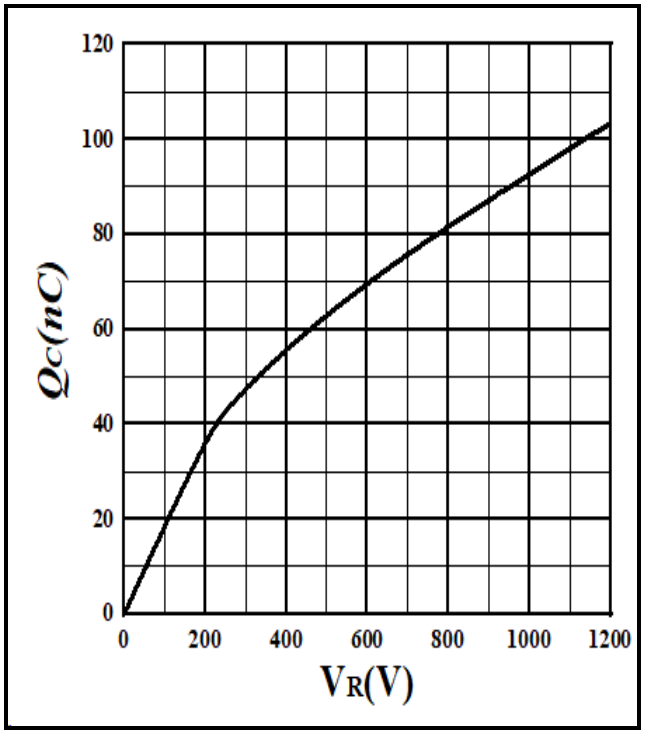
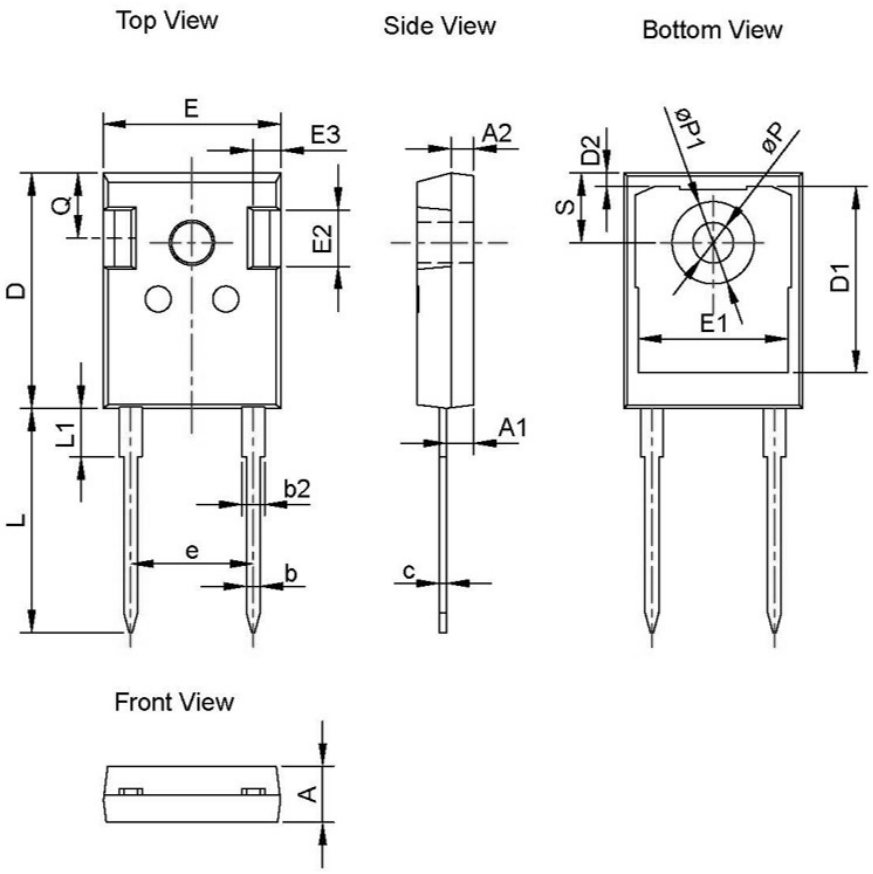


Figure 7. Total capacitance charge vs. reverse voltage

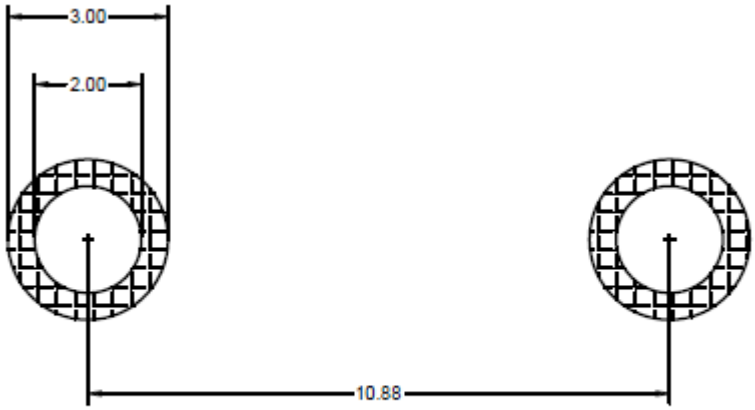
Package Information



Dimension unit: [mm]			
Symbol	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
c	0.51	0.60	0.75
D	20.70	21.00	21.30
D1	16.25	16.55	16.85
D2	1.00	1.20	1.35
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	10.88 BSC		
L	19.62	19.92	20.22
L1	-	-	4.30
øP	3.40	3.60	3.80
øP1	-	-	7.30
Q	5.40	5.80	6.20
S	6.20 BSC		

Recommended Solder Pad Layout

Note: All dimensions are in mm



TO-247-2L

Ordering Information

Part number	SDS120J015H3-ISATH
Package	TO-247-2L
Unit quantity	300 EA
Packing type	Tube

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